

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s):

Garlapati et al.

Title:

VOLTAGE REFERENCE GENERATOR CIRCUIT USING LOW-BETA

EFFECT OF A CMOS BIPOLAR TRANSISTOR

Application No.: 10/813,837

Filed:

March 31, 2004

Examiner:

Not yet assigned

Group Art Unit: 2819

Atty. Docket No.: 026-0044

July 14, 2004

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INFORMATION DISCLOSURE STATEMENT 37 C.F.R. § 1.97(b)

Dear Sir:

Pursuant to 37 C.F.R. § 1.56, § 1.97 and § 1.98, the undersigned brings the patents, publications, applications or other information identified in the attached:

\boxtimes	Form(s) PTO-1449 (2 pages), including copy(ies) of 9 reference(s).
	Other:

to the Examiner's attention in the above-identified application. Citation of such information shall not be construed as:

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- 2. a representation that a search has been made, other than as described below; or
- 3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in § 1.56(b).

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For each item of information listed that is not in the English language, the undersigned has provided a concise explanation of the relevance through (i) an English language abstract, (ii) an English language equivalent application, or (iii) if cited in a search report or other action PATENT

by a foreign patent office in a counterpart foreign application, an English language version of the search report or action that indicates the degree of relevance found by the foreign office.

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This Information Disclosure Statement is filed within three months of the filing
date of a national application other than a continued prosecution application under
§ 1.53(d) or within three months of entry of the national stage as set forth in
§ 1.491 in an international application. Therefore, no fee is required.

The undersigned believes that this Information Disclosure Statement is being filed before the mailing date of a first Office action on the merits or before the mailing date of a first Office action after the filing of a request for continued examination under § 1.114. Therefore, no fee is believed required.

If however, this Information Disclosure Statement is filed after the period specified in § 1.97(b), the undersigned hereby authorizes the Commissioner to charge the fee set forth in § 1.17(p) to Deposit Account No. 50-0631.

CERTIFICATE	OF	MAILING	OR TR	ANSMISSI	ON
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Respectfully submitted,

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U.S. Departm	ent of Cor	mmerce, Patent and Trademark	Office		Attorney Docket No.:	026-0044			
					Application No.:	10/813,837			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant(s): Garlapati et				
(Use several sheets if necessary)					Filing Date:	March 31, 2004			
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